DISCRETE SEMICONDUCTORS

DATA SHEET

BT300S series
Thyristors

Product specification

September 1997

WeEn

WeEn Semiconductors

GENERAL DESCRIPTION

Glass passivated thyristors in a plastic envelope, suitable for surface mounting, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

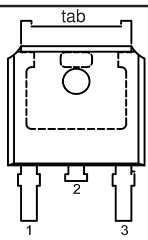
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT300S (or BT300M)**-**	**500R**	**600R**	**800R**	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages	500	600	800	V
$I_{T(AV)}$	Average on-state current	5	5	5	A
$I_{T(RMS)}$	RMS on-state current	8	8	8	A
I_{TSM}	Non-repetitive peak on-state current	65	65	65	A

PINNING - SOT428

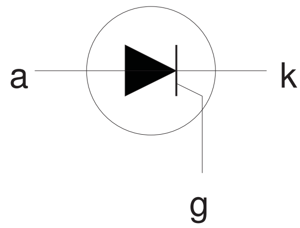
PIN NUMBER	Standard S	Alternative M
1	cathode	gate
2	anode	anode
3	gate	cathode
tab	anode	anode

PIN CONFIGURATION



DPAK (SOT428)

SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500R	-600R	-800R	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages		-	500[1]	600[1]	800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 107$ ˚C	-	5			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	8			A
I_{TSM}	Non-repetitive peak on-state current	half sine wave; $T_j = 25$ ˚C prior to surge					
		t = 10 ms	-	65			A
		t = 8.3 ms	-	71			A
I^2t	I^2t for fusing	t = 10 ms	-	21			A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 10$ A; $I_G = 50$ mA; $dI_G/dt = 50$ mA/µs	-	50			A/µs
I_{GM}	Peak gate current		-	2			A
V_{GM}	Peak gate voltage		-	5			V
V_{RGM}	Peak reverse gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			˚C
T_j	Operating junction temperature		-	125			˚C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	2.2	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	pcb (FR4) mounted; footprint as in Fig.14	-	75	-	K/W

STATIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	V_D = 12 V; I_T = 0.1 A	-	2	15	mA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A	-	10	40	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A	-	10	20	mA
V_T	On-state voltage	I_T = 12 A	-	1.35	1.6	V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$; I_T = 0.1 A; T_j = 125 ˚C	0.25	0.4	-	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}$; $V_R = V_{RRM(max)}$; T_j = 125 ˚C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 ˚C; exponential waveform.				
		Gate open circuit	50	100	-	V/µs
		R_{GK} = 100 Ω	200	1000	-	V/µs
t_{gt}	Gate controlled turn-on time	I_{TM} = 10 A; $V_D = V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	µs
t_q	Circuit commutated turn-off time	V_D = 67% $V_{DRM(max)}$; T_j = 125 ˚C; I_{TM} = 12 A; V_R = 25 V; dI_{TM}/dt = 30 A/µs; dV_D/dt = 50 V/µs; R_{GK} = 100 Ω	-	70	-	µs

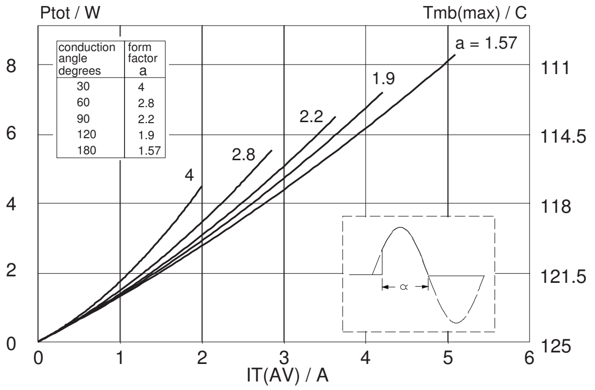


Fig.1. Maximum on-state dissipation, P_{tot}, versus average on-state current, $I_{T(AV)}$, where a = form factor = $I_{T(RMS)}$/ $I_{T(AV)}$.

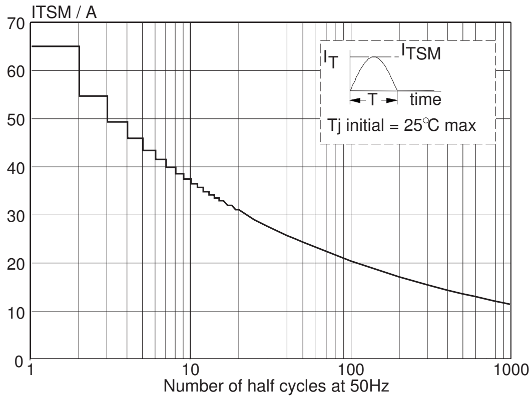


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

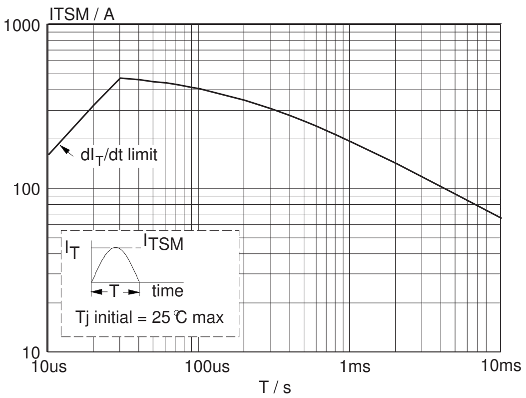


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus pulse width t_p, for sinusoidal currents, $t_p \leq 10ms$.

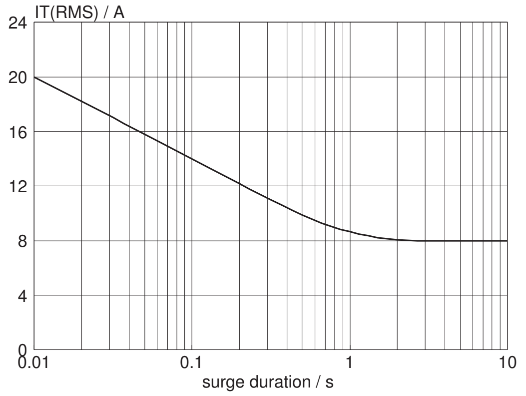


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \leq 107˚C$.

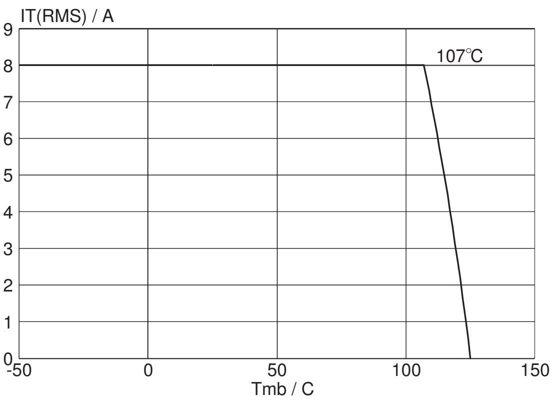


Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb}.

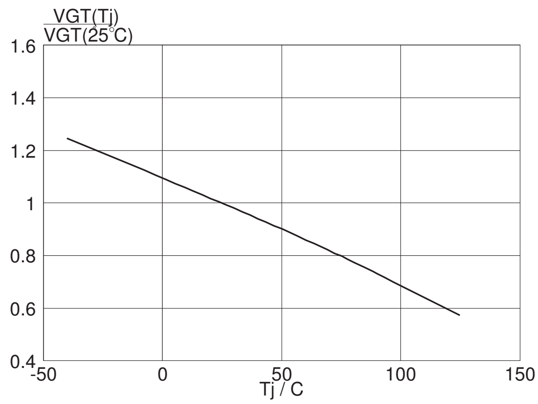


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)$/ $V_{GT}(25˚C)$, versus junction temperature T_j.

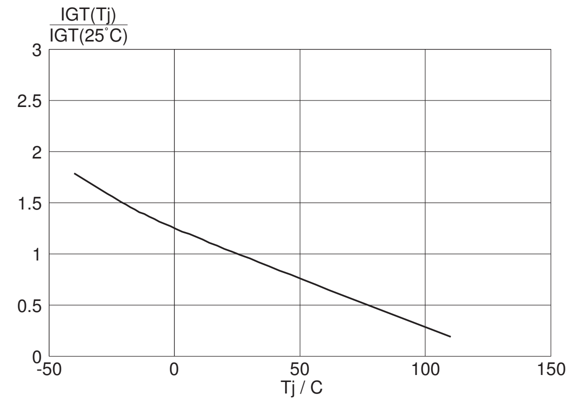


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/ I_{GT}(25˚C)$, versus junction temperature T_j.

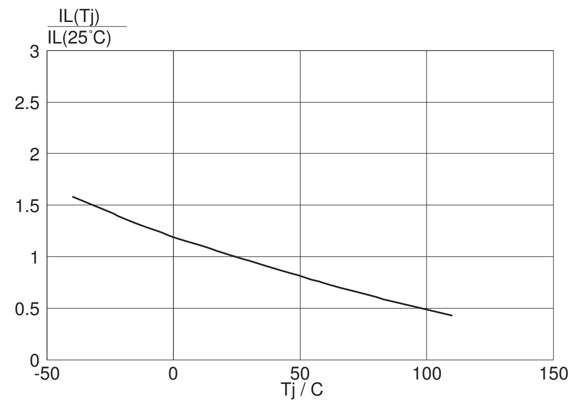


Fig.8. Normalised latching current $I_L(T_j)/ I_L(25˚C)$, versus junction temperature T_j.

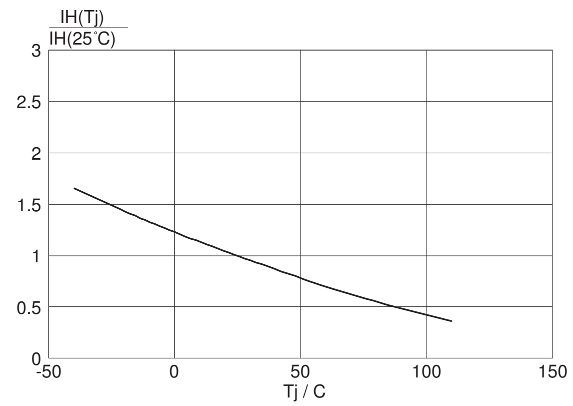


Fig.9. Normalised holding current $I_H(T_j)/ I_H(25˚C)$, versus junction temperature T_j.

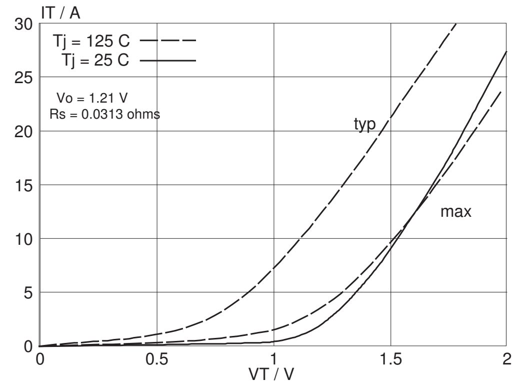


Fig.10. Typical and maximum on-state characteristic.

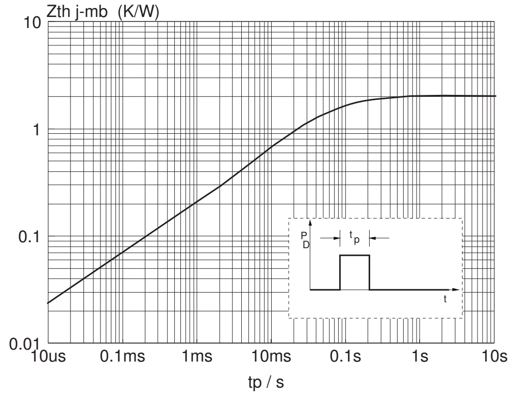


Fig.11. Transient thermal impedance $Z_{th\ j\text{-}mb}$, versus pulse width t_p.

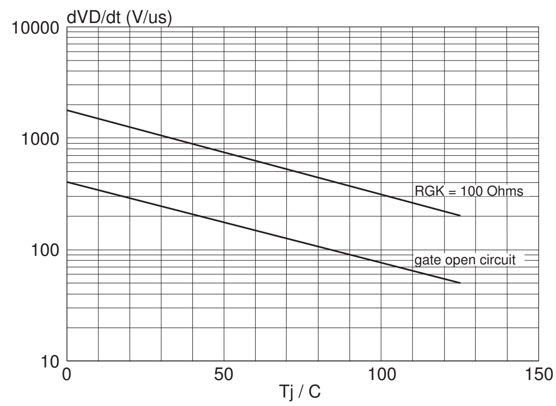
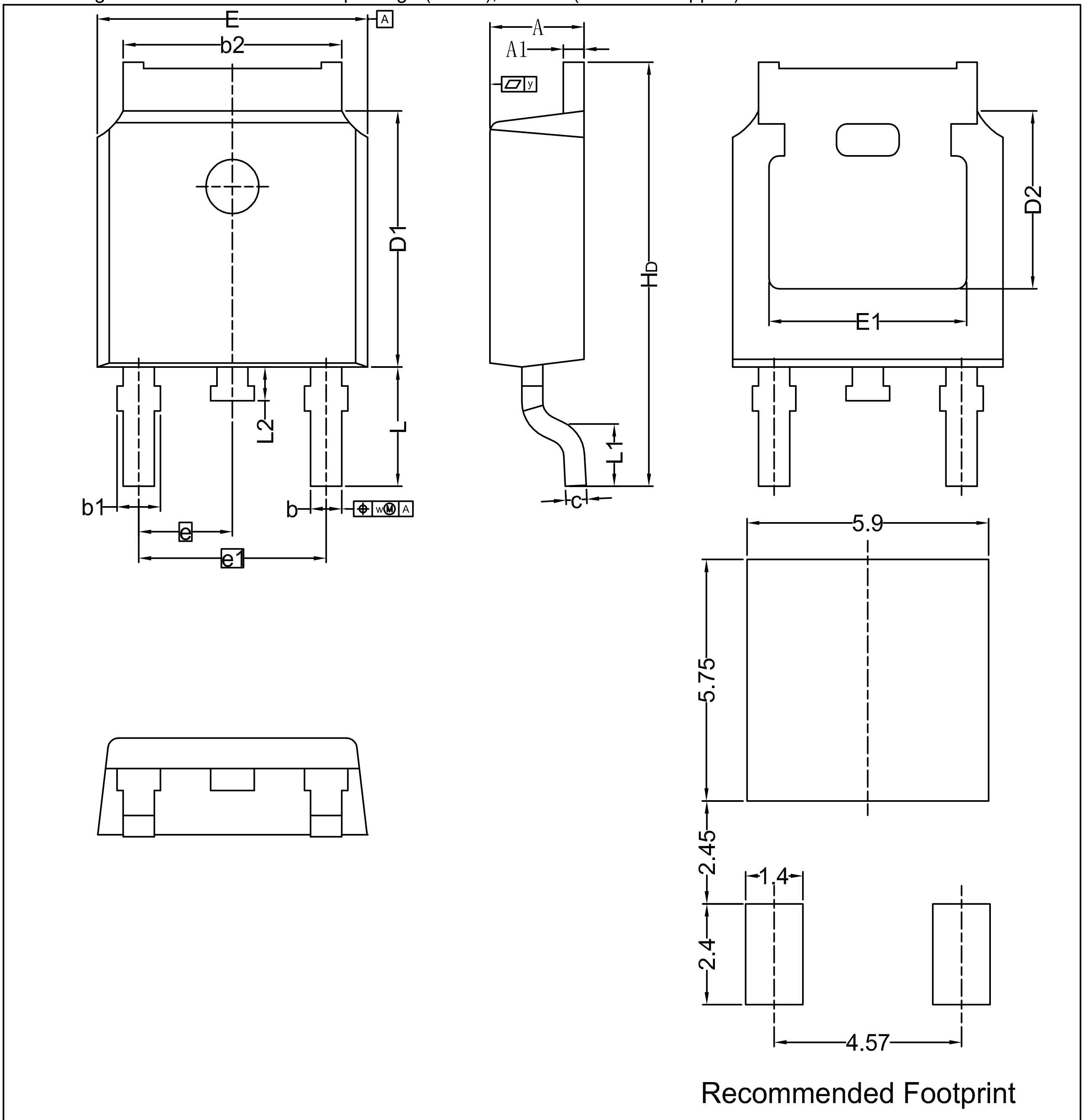


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

MECHANICAL DATA

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) TO252



Unit		A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H_D	L	L1	L2	w	y
mm	min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45			9.60		0.50	0.50		
	nom											2.285	4.57		2.90 (Ref.)			0.20	
	max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40		---	0.90		0.20

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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